

Ultrahigh Threshold Voltage Depletion-Mode Power MOSFET

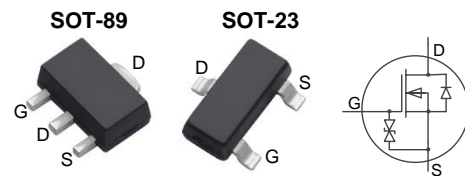
General Features

- ESD improved Capability
- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Proprietary Advanced Ultrahigh V_{th} Technology
- RoHS Compliant
- Halogen-free available

BV _{DSX}	V _{GS(off),min}	I _{DSS,min}
70V	-25V	120mA

Applications

- Quick Charge (QC4.0)/ Type C PD Charger or Adapter
- Current Source
- Voltage Source



General Description

DMZ0615E/ DMX0615E / DMZ0622E/ DMX0622E /DMX1015E- novel series of depletion mode MOSFETs are designed with ARK Microelectronics proprietary and patent ultrahigh threshold voltage technology. DMZ0622E is a wide range voltage (up to 70V) regulator. Its input voltage can be 70V high, and it also can provide stable output voltage from about 11V to 23V in accordance with different work conditions. It is very suitable for Quick Charge (QC4.0) / Type C PD Charger application which have variable charging voltage output (5-20V).

By using the sub threshold characteristics, the depletion mode MOSFET DMZ0622E can provide stable power to the load, and the voltage of load can be clamped to protect the load without zener diode.

DMZ0622E can endure wide voltage input up to 70V, and can provide with proper voltage to the load. These characteristics are fit for the application of Quick Charge (QC4.0) /Type C PD Charger, and its PWM control IC need to be powered with stable voltage.

Ordering Information

Part Number	Package	Marking	Remark
DMZ0622E	SOT-23	0622	Halogen Free
DMX0622E	SOT-89	0622	Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	DMZ0622E	DMX0622E	Unit
V _{DSX}	Drain-to-Source Voltage ^[1]	70		V
V _{DGX}	Drain-to-Gate Voltage ^[1]	70		V
I _D	Continuous Drain Current	0.1		A
I _{DM}	Pulsed Drain Current ^[2]	0.4		
P _D	Power Dissipation	0.5	1.0	W
V _{GS}	Gate-to-Source Voltage	±30		V
V _{ESD(G-S)}	Gate Source ESD IEC, C=150pF, R=330Ω	400		V
T _L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300		°C
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMZ0622E	DMX0622E	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	125	K/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	70	--	--	V	$V_{GS} = -30\text{V}$, $I_D = 250\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	15	μA	$V_{DS} = 70\text{V}$, $V_{GS} = -30\text{V}$
		--	--	1.0	mA	$V_{DS} = 70\text{V}$, $V_{GS} = -30\text{V}$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	μA	$V_{GS} = +30\text{V}$, $V_{DS} = 0\text{V}$
		--	--	-20		$V_{GS} = -30\text{V}$, $V_{DS} = 0\text{V}$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	120	--	--	mA	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	10	15	Ω	$V_{GS} = 0\text{V}$, $I_D = 100\text{mA}$ [3]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-19	-22	-25	V	$V_{DS} = 20\text{V}$, $I_D = 8\mu\text{A}$
gfs	Forward Transconductance	--	130	--	mS	$V_{DS} = 20\text{V}$, $I_D = 5\text{mA}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	1.5	--	pF	$V_{GS} = -30\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$
C_{OSS}	Output Capacitance	--	2.6	--		
C_{RSS}	Reverse Transfer Capacitance	--	0.74	--		
Q_G	Total Gate Charge	--	9	--	nC	$V_{GS} = -30\text{V} \sim 0\text{V}$ $V_{DS} = 30\text{V}$, $I_D = 100\text{mA}$
Q_{GS}	Gate-to-Source Charge	--	1.5	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	2.3	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	17	--	us	$V_{GS} = -30\text{V} \sim 0\text{V}$ $V_{DD} = 35\text{V}$, $I_D = 100\text{mA}$ $R_G = 20\Omega$
t_{rise}	Rise Time	--	200	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	11	--		
t_{fall}	Fall Time	--	4	--		

Source-Drain Diode Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 100\text{mA}$, $V_{GS} = -30\text{V}$

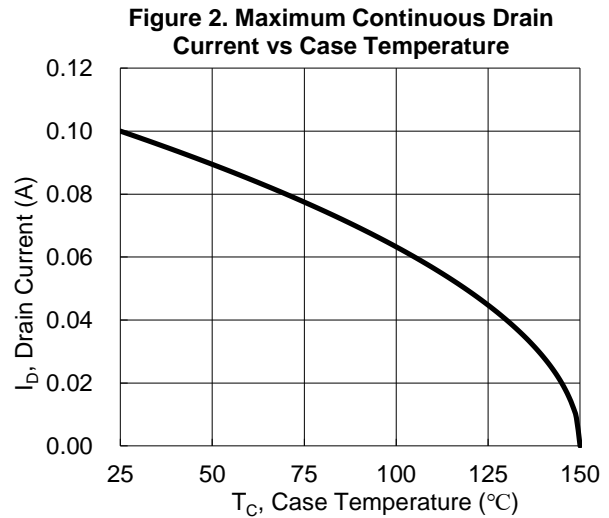
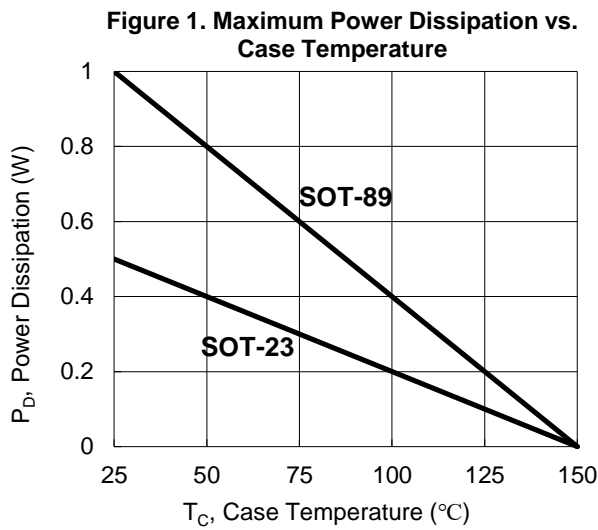
NOTE:

[1] $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

Typical and highlight Characteristics



DMZ0622E/DMX0622E can be used as a current or voltage source to supply power to the load, as shown in Figure 3.

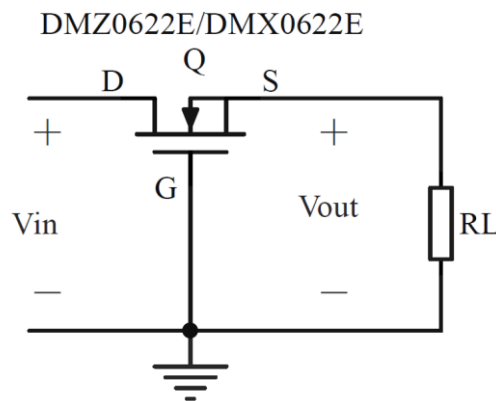
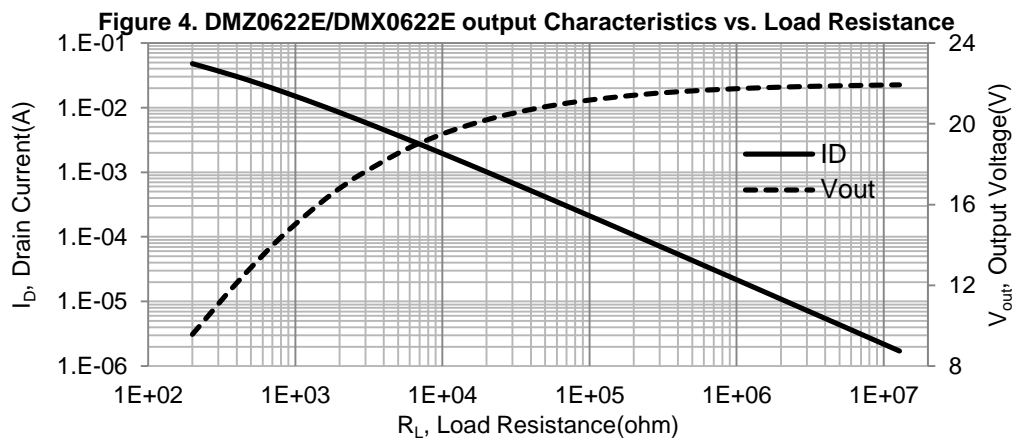


Figure 3. DMZ0622E/DMX0622E as a voltage source

The output voltage V_{out} is determined by the load R_L, current I_D and V_{GS(OFF)} ∴

$$I_D = I_{DSS} \left(1 + I_D R_L / V_{GS(OFF)} \right)^2$$

$$V_{out} = -V_{GS} = I_D R_L$$



From the above function, we can see the depletion mode MOSFET operate in sub-threshold region, the V_{out} is always below or closed to the threshold voltage or Gate-to-Source Cut-off Voltage $V_{GS(OFF)}$, no matter how the input voltage V_{in} changes. Therefore, in addition to provide power for load like IC, the output voltage V_{out} can be clamped to the $V_{GS(OFF)}$, the IC is then protected from variable voltage or current. DMZ0622E/DMX0622E can support up to 70V input voltage. V_{out} and V_{in} have relations following the formulas:

If $V_{in} < |V_{GS(OFF)}|$, then $V_{out} \approx V_{in}$

If $V_{in} \geq |V_{GS(OFF)}|$, then $V_{out} \leq V_{GS(OFF)}$

The Ultrahigh Threshold Voltage Depletion Mode Power MOSFET--DMZ0622E/DMX0622E, was developed by ARK Microelectronics proprietary and patent technology. The threshold voltage $V_{GS(OFF)}$ of DMZ0622E/DMX0622E is between -19V and -25V, can provide sufficient voltage for load such like a PWM IC in the primary side of a Flyback converter.

Since DMZ0622E/DMX0622E has a variation distribution of $V_{GS(OFF)}$, from -19V to -25V, so its output voltage is different with different $V_{GS(OFF)}$. Figure 5 shows the characteristics of output voltage V_{out} vs. junction temperature of two DMZ0622E/DMX0622E MOSFETS which has the highest $V_{GS(OFF)}$,=-19V and lowest $V_{GS(OFF)}$,=-25V respectively. This means the clamped voltage of V_{out} will also change with temperature and $V_{GS(OFF)}$.

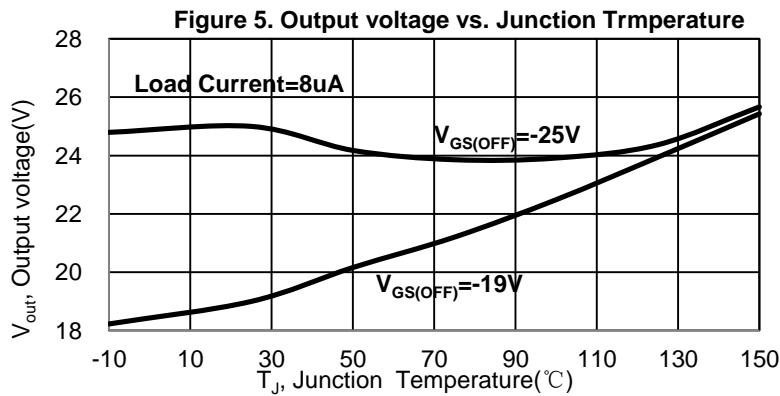
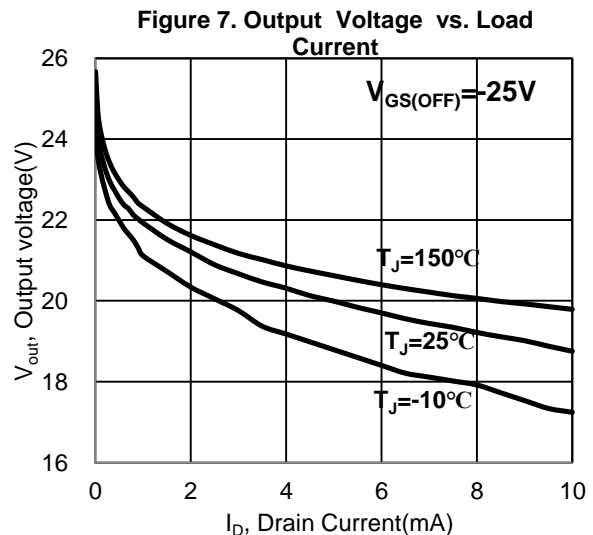
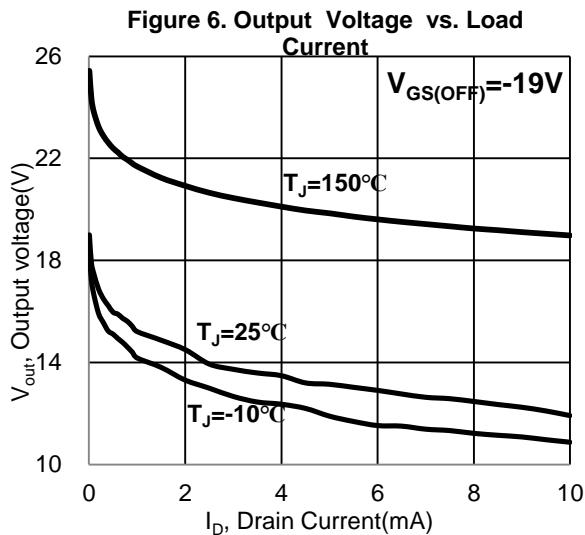


Fig 6 and Fig 7 shows the characteristics of output voltage V_{out} vs. load current I_{RL} and junction temperature T_J of two DMZ0622E/DMX0622E MOSFETS which has the highest $V_{GS(OFF)}$,=-19V and lowest $V_{GS(OFF)}$,=-25V respectively.



Typical applications:

Figure 8 is a typical schematic of a primary side of a Flyback power source, it serves as a quick charger with TypeC PD or Quick Charge (QC) protocols. These kind of quick chargers can provide variable charging voltage (from 5-20V) output, these voltages will turn back to the primary side, so that the voltage of auxiliary coil, which is used as a power source to PWM IC has to be changed in a wide ranges, even it can be too high to use for PWM IC. The normal solution is using a transistor and zener diode and some resistors to provide PWM IC with stable voltage. But the circuit is complicated and the BOM cost is higher.

The alternate cost effective solution is represent in Figure 9. The transistor, zener diode and resistors in Figure 8 can be simply replaced with DMZ0622E/DMX0622E, then the space of PCB is saved with fewer components, and the cost will be down.

The depletion mode MOSFET DMZ6005E is used for start-up, when the charger start to work, the auxiliary coil will supply voltage for the PWM IC, then DMZ6005E is shut off, so that the standby power disipation of system will be significantly low. The documents of DMZ6005E can be accessed in ARK's website.

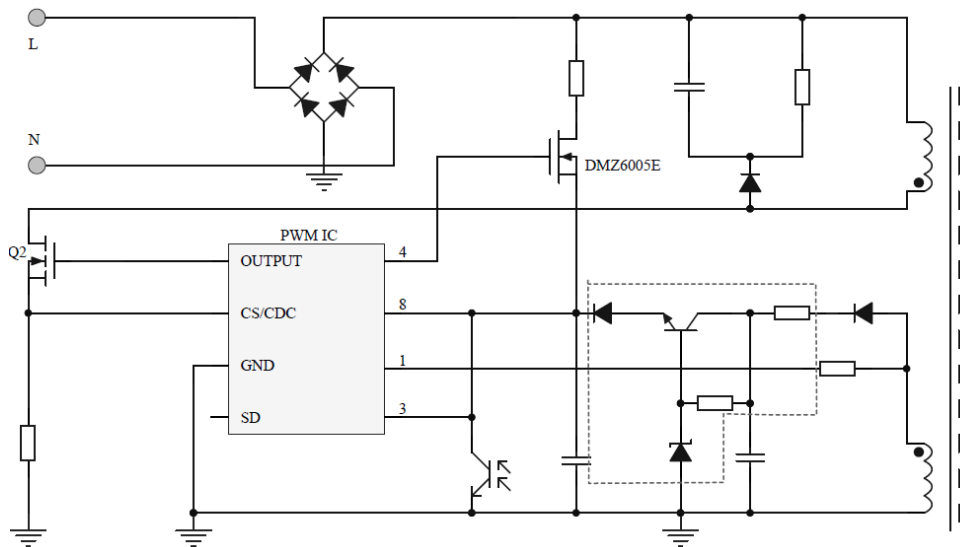


Figure 8. Normal circuit with transistor and diode

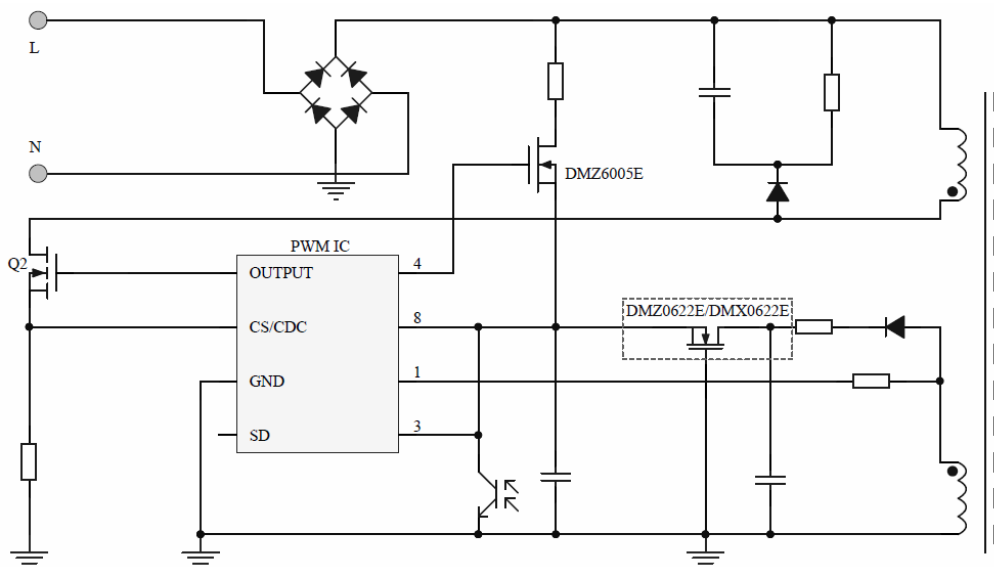
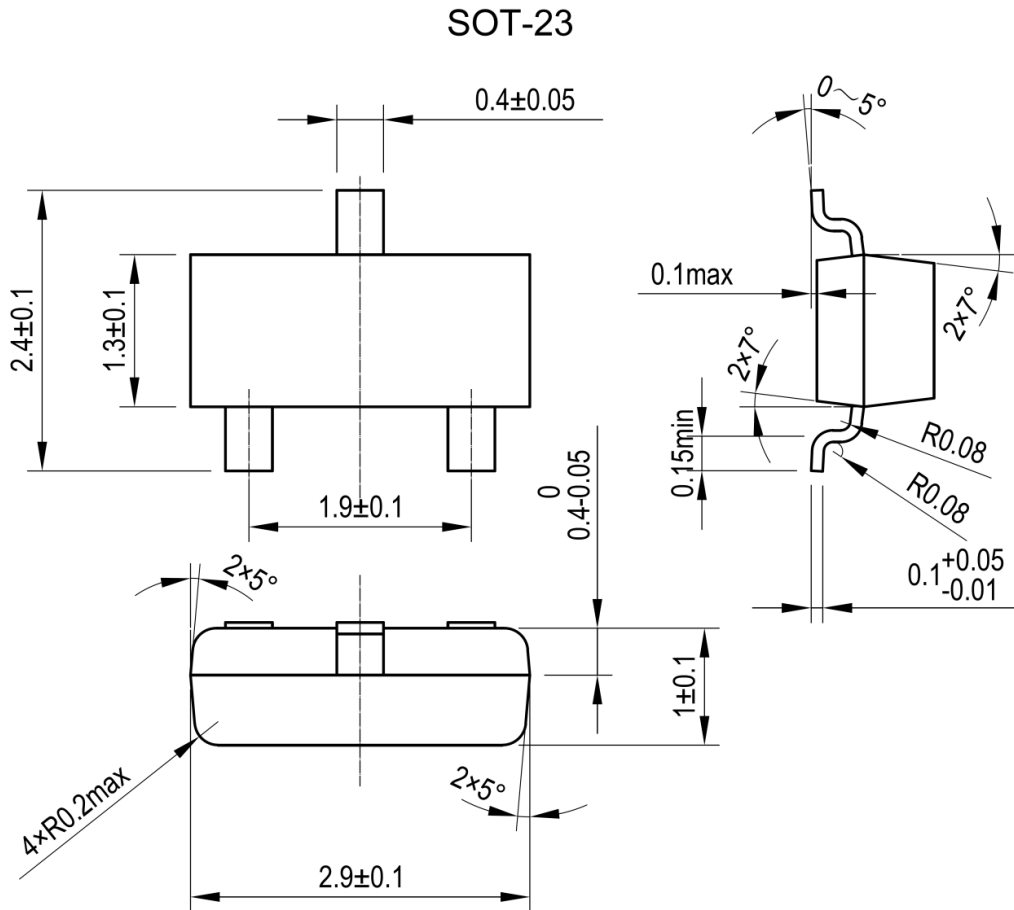
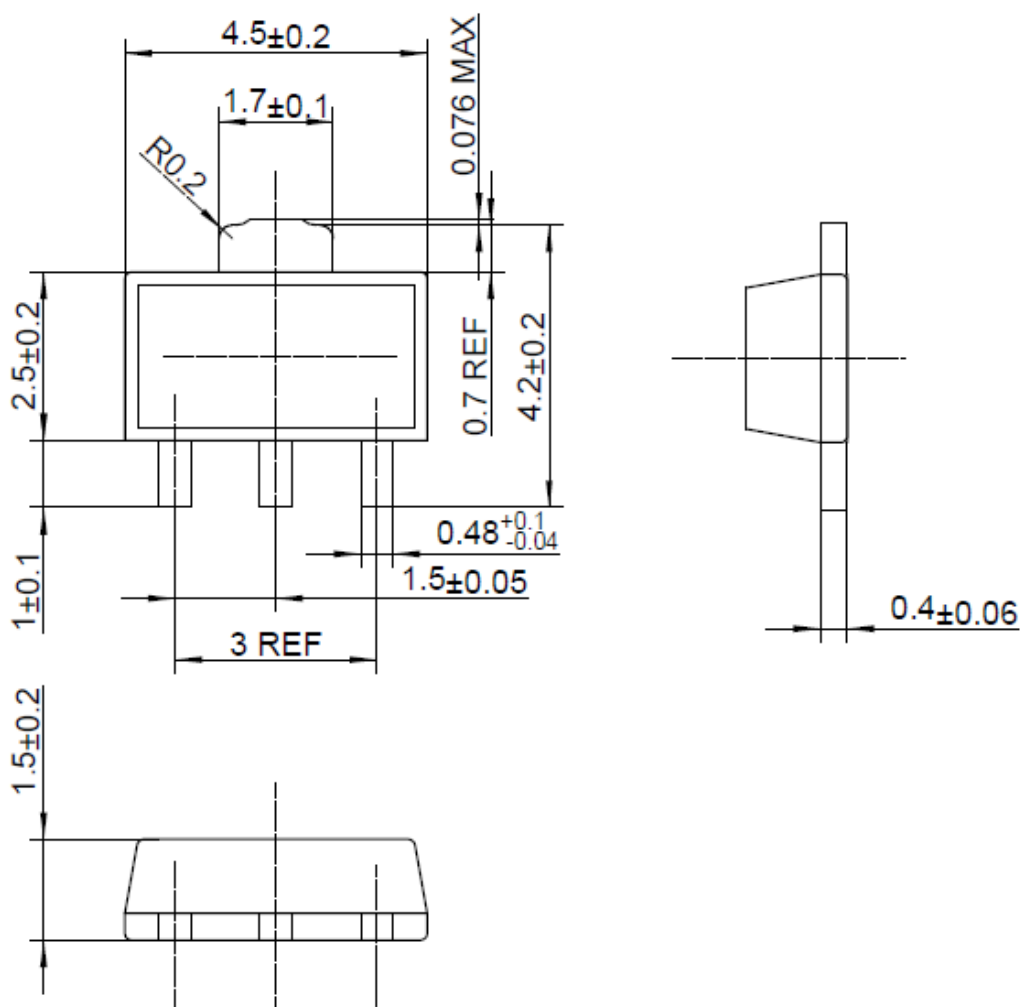


Figure 9. Circuit with DMZ0622E/DMX0622E

Package Dimensions



SOT-89





Published by

ARK Microelectronics Co., Ltd.
ADD: 4F, D26, UESTC National Science Park No. 1 Shuangxing Avenue, Gongxing Street,
Shuangliu District, Chengdu, China (Sichuan) Pilot Free Trade Zone.
Tel: +86-28-8523-2215 Email: sales@ark-micro.com <http://www.ark-micro.com>

All Rights Reserved

Disclaimers

ARK Microelectronics Co., Ltd. reserves the right to make change without notice in order to improve reliability, function or design and to discontinue any product or service without notice. Customers should obtain the latest relevant information before orders and should verify that such information is current and complete. All products are sold subject to ARK Microelectronics Co., Ltd.'s terms and conditions supplied at the time of order acknowledgement.

ARK Microelectronics Co., Ltd. warrants performance of its hardware products to the specifications at the time of sale, Testing, reliability and quality control are used to the extent ARK Microelectronics Co., Ltd deems necessary to support this warrantee. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessary performed.

ARK Microelectronics Co., Ltd. does not assume any liability arising from the use of any product or circuit designs described herein. Customers are responsible for their products and applications using ARK Microelectronics Co., Ltd.'s components. To minimize risk, customers must provide adequate design and operating safeguards.

ARK Microelectronics Co., Ltd. does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information in ARK Microelectronics Co., Ltd.'s data sheets or data books is permissible only if reproduction is without modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. ARK Microelectronics Co., Ltd is not responsible or liable for such altered documentation.

Resale of ARK Microelectronics Co., Ltd.'s products with statements different from or beyond the parameters stated by ARK Microelectronics Co., Ltd. for the product or service voids all express or implied warranties for the associated ARK Microelectronics Co., Ltd.'s product or service and is unfair and deceptive business practice. ARK Microelectronics Co., Ltd is not responsible or liable for any such statements.

Life Support Policy:

ARK Microelectronics Co., Ltd.'s products are not authorized for use as critical components in life devices or systems without the expressed written approval of ARK Microelectronics Co., Ltd.

As used herein:

1. Life support devices or systems are devices or systems which:
 - a. are intended for surgical implant into the human body,
 - b. support or sustain life,
 - c. whose failure to perform when properly used in accordance with instructions for used provided in the labeling, can be reasonably expected to result in significant injury to the user.
 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.
-